

## 1 Scope

The present specifications shall apply to Sanken silicon diode, RM4Y.

## 2 Outline

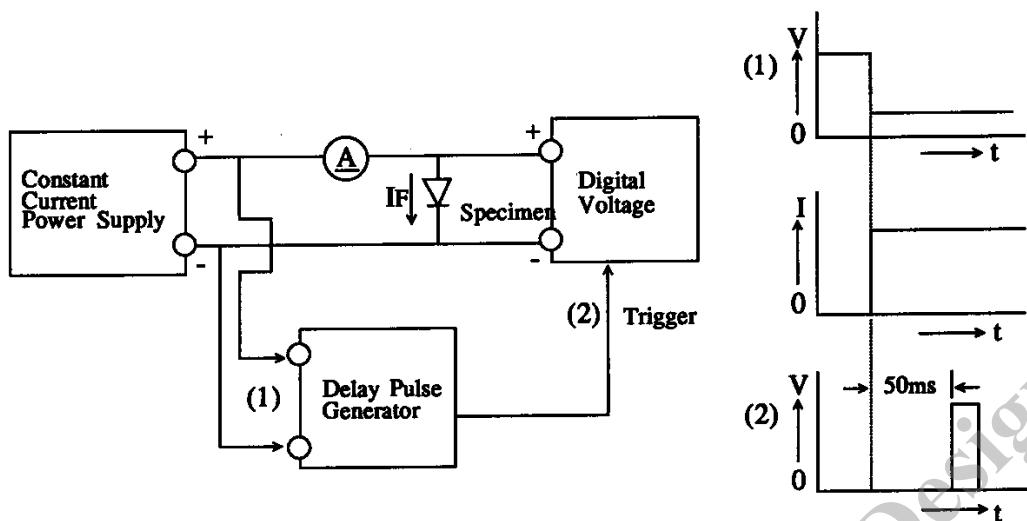
|              |  |                                    |
|--------------|--|------------------------------------|
| Type         | Silicon Rectifier Diode (Mesa type)      |                                    |
| Structure    | Resin Molded                             | Flammability: UL94V-0 (Equivalent) |
| Applications | Commercial Frequency Rectification, etc. |                                    |

## 3 Absolute maximum ratings

| No. | Item                           | Symbol      | Unit | Rating      | Conditions                           |
|-----|--------------------------------|-------------|------|-------------|--------------------------------------|
| 1   | Transient Peak Reverse Voltage | $V_{RSM}$   | V    | 150         |                                      |
| 2   | Peak Reverse Voltage           | $V_{RM}$    | V    | 100         |                                      |
| 3   | Average Forward Current        | $I_{F(AV)}$ | A    | 3.0         | Refer to derating curve in Section 6 |
| 4   | Peak Surge Forward Current     | $I_{FSM}$   | A    | 200         | 10ms. Half sine wave, one shot       |
| 5   | Junction Temperature           | $T_j$       | °C   | -40 to +150 |                                      |
| 6   | Storage Temperature            | $T_{stg}$   | °C   | -40 to +150 |                                      |

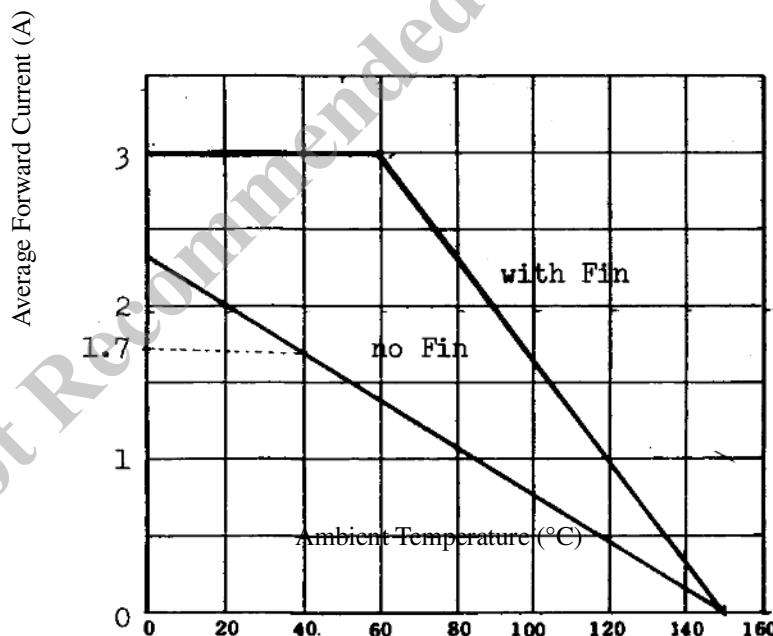
## 4 Electrical characteristics ( $T_a=25^\circ\text{C}$ , unless otherwise specified)

| No. | Item   | Symbol        | Unit | Rating    | Conditions                          |
|-----|--|---------------|------|-----------|-------------------------------------|
| 1   | Forward Voltage Drop                           | $V_F$         | V    | 0.95 max. | $I_F=3.0\text{A}$                   |
| 2   | Reverse Leakage Current                        | $I_R$         | μA   | 10 max.   | $V_R=V_{RM}$                        |
| 3   | Reverse Leakage Current Under High Temperature | $H \cdot I_R$ | μA   | 50 max.   | $V_R=V_{RM}, T_j=150^\circ\text{C}$ |
| 4   | Thermal Resistance                             | $R_{th(j-l)}$ | °C/W | 8.0 max.  | Between Junction and Lead           |

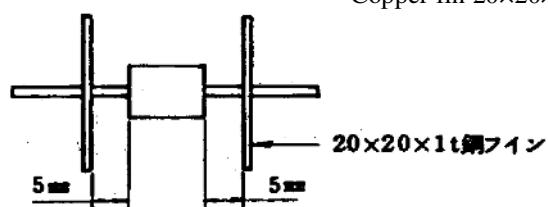
5  $V_F$  test and test circuit

## 6 Derating

Derating to the ambient temperature  
Power loss generated by voltage is not taken into consideration.

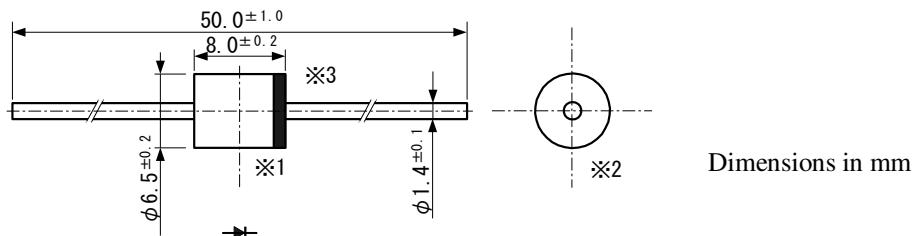


Copper fin 20×20×1t



## 7 Dimensions, inner structure and marking

## 7-1 Dimensions refer



\*1 The allowance position of body against the center of whole lead wire is 0.5mm (max.)

\*2 The centric allowance of lead wire against center of physical body is 0.3mm (max.)

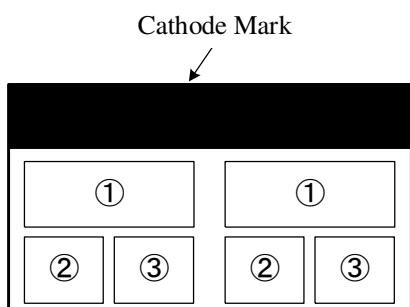
\*3 The burr may exist up to 2mm from the body of lead.

## 7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

The color of the case will be black.

## 7-3 Marking



① Type number RM4Y

② Lot number 1

First digit: Last digit of Year

Second digit: Month

From 1 to 9 for Jan. to Sep.

O for Oct., N for Nov., and D for Dec.

③ Lot number 2 (ten days)

• Top of the month

.. Middle of month

... End of month

The color of marking must be white